Antoni Rogalski

List of Publications by Year
in descending order

288	11,599	61984 43	31849 101
papers	citations	h-index	g-index

296	296	296	7859
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	16th International Workshop on Advanced Infrared Technology and Applications (AITA 2021). Engineering Proceedings, 2022, 8, .	0.4	0
2	Van der Waals two-color infrared detection. Light: Science and Applications, 2022, 11, 27.	16.6	3
3	Interband Quantum Cascade Infrared Photodetectors: Current Status and Future Trends. Physical Review Applied, 2022, 17, .	3.8	14
4	Figure of merit for infrared detector materials. Infrared Physics and Technology, 2022, 122, 104063.	2.9	5
5	Detectivities of WS2/HfS2 heterojunctions. Nature Nanotechnology, 2022, 17, 217-219.	31.5	12
6	New insights into the ultimate performance of HgCdTe photodiodes. Sensors and Actuators A: Physical, 2022, 339, 113511.	4.1	23
7	Performance Evaluation of Type-II Superlattice Devices Relative to HgCdTe Photodiodes. IEEE Transactions on Electron Devices, 2022, 69, 2992-3002.	3.0	4
8	Erratum to â€œPerformance Evaluation of Type-II Superlattice Devices Relative to HgCdTe Photodiodesâ€• [Jun 22 2992-3002]. IEEE Transactions on Electron Devices, 2022, 69, 4050-4050.	3.0	0
9	Trends in Performance Limits of the HOT Infrared Photodetectors. Applied Sciences (Switzerland), 2021, 11, 501.	2.5	48
10	Progress in Quantum Dot Infrared Photodetectors. Lecture Notes in Nanoscale Science and Technology, 2021, , 1-74.	0.8	3
11	Uncertainty in the estimation of the InAs1âˆ’xSbx intrinsic carrier concentration. Infrared Physics and Technology, 2021, 117, 103854.	2.9	0
12	Enhanced Performance of HgCdTe Midwavelength Infrared Electron Avalanche Photodetectors With Guard Ring Designs. IEEE Transactions on Electron Devices, 2020, 67, 542-546.	3.0	19
13	HgCdTe photodetectors. , 2020, , 235-335.		12
14	Higher Operating Temperature IR Detectors of the MOCVD Grown HgCdTe Heterostructures. Journal of Electronic Materials, 2020, 49, 6908-6917.	2.2	7
15	InAsSb-Based Infrared Photodetectors: Thirty Years Later On. Sensors, 2020, 20, 7047.	3.8	46
16	Locallyâ€Strainâ€Induced Heavyâ€Holeâ€Band Splitting Observed in Mobility Spectrum of pâ€Type InAs Grown on GaAs. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900604.	2.4	8
17	Enhanced Performance of HgCdTe Long-Wavelength Infrared Photodetectors With nBn Design. IEEE Transactions on Electron Devices, 2020, 67, 2001-2007.	3.0	18
18	Comparison of performance limits of HOT HgCdTe photodiodes and colloidal quantum dot infrared detectors. , 2020, , .		3

#	Article	IF	Citations
19	Advanced Infrared Technology and Applications 2020: introduction to the feature issue. Applied Optics, 2020, 59, AIT1.	1.8	1
20	Infrared Detector Characterization. , 2020, , 15-34.		0
21	Fundamental Detector Performance Limits. , 2020, , 35-68.		0
22	Graphene-Based Detectors. , 2020, , 141-192.		0
23	Colloidal Quantum Dot Infrared Detectors. , 2020, , 217-232.		0
24	Demonstration of the Very Long Wavelength Infrared Type-II Superlattice InAs/InAsSb GaAs Immersed Photodetector Operating at Thermoelectric Cooling. IEEE Electron Device Letters, 2019, 40, 1396-1398.	3.9	14
25	Type-II superlattice photodetectors versus HgCdTe photodiodes. Progress in Quantum Electronics, 2019, 68, 100228.	7.0	81
26	Bandgap energy determination of InAsSb epilayers grown by molecular beam epitaxy on GaAs substrates. Progress in Natural Science: Materials International, 2019, 29, 472-476.	4.4	15
27	Trap parameters in the infrared InAsSb absorber found by capacitance and noise measurements. Semiconductor Science and Technology, 2019, 34, 105017.	2.0	4
28	Sensing Infrared Photons at Room Temperature: From Bulk Materials to Atomic Layers. Small, 2019, 15, e1904396.	10.0	83
29	Two-dimensional infrared and terahertz detectors: Outlook and status. Applied Physics Reviews, 2019, 6, .	11.3	94
30	2D Materials in Infrared Detector Family. Proceedings (mdpi), 2019, 27, 33.	0.2	3
31	Photon recycling effect in small pixel p-i-n HgCdTe long wavelength infrared photodiodes. Infrared Physics and Technology, 2019, 97, 38-42.	2.9	17
32	Graphene-based materials in the infrared and terahertz detector families: a tutorial. Advances in Optics and Photonics, 2019, 11, 314.	25.5	53
33	Type-II superlattice photodetectors versus HgCdTe photodiodes. , 2019, , .		4
34	Investigation on the InAs_{1â€“x}Sb_xepilayers growth on GaAs (001) substrate by molecular beam epitaxy. Journal of Semiconductors, 2018, 39, 033003.	3.7	9
35	Interfacial Misfit Array Technique for GaSb Growth on GaAs (001) Substrate by Molecular Beam Epitaxy. Journal of Electronic Materials, 2018, 47, 299-304.	2.2	19
36	Optimization of the interfacial misfit array growth mode of GaSb epilayers on GaAs substrate. Journal of Crystal Growth, 2018, 483, 26-30.	1.5	15

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37	Electrical Properties of Midwave and Longwave InAs/GaSb Superlattices Grown on GaAs Substrates by Molecular Beam Epitaxy. Nanoscale Research Letters, 2018, 13, 196.	5.7	10
38	Investigation of surface leakage current in MWIR HgCdTe and InAsSb barrier detectors. Semiconductor Science and Technology, 2018, 33, 125010.	2.0	15
39	Demonstration of HOT LWIR T2SLs InAs/InAsSb photodetectors grown on GaAs substrate. Infrared Physics and Technology, 2018, 95, 222-226.	2.9	22
40	Terahertz Detectors. , 2018, , 418-431.		2
41	Advanced Infrared Technology and Applications: introduction. Applied Optics, 2018, 57, AITA1.	1.8	3
42	Performance prediction of p-i-n HgCdTe long-wavelength infrared HOT photodiodes. Applied Optics, 2018, 57, D11.	1.8	21
43	High-operating temperature InAsSb/AlSb heterostructure infrared detectors grown on GaAs substrates by molecular beam epitaxy. Optical Engineering, 2018, 57, 1.	1.0	3
44	Electrical and optical performance of midwave infrared InAsSb heterostructure detectors. Optical Engineering, 2018, 57, 1.	1.0	6
45	Long term stability study of InAsSb mid-wave infrared HOT detectors passivated through two step passivation technique. , 2018, , .		2
46	Antimonide-based Infrared Detectors: A New Perspective. , 2018, , .		36
47	Study of the Effectiveness of Anodic Films as Surface Passivation for InAsSb Mid-Wave Infrared HOT Detectors. Acta Physica Polonica A, 2018, 134, 981-985.	0.5	2
48	Influence of radiative recombination on performance of p-i-n HOT long wavelength infrared HgCdTe photodiodes. , 2018, , .		0
49	Structural and optical characterization of the high quality Be-doped InAs epitaxial layer grown on GaAs substrate. , 2018, , .		1
50	High-operating temperatures InAsSb/AlSb heterostructure infrared detectors. , 2018, , .		0
51	Investigation of hillocks formation on (1 0 0) HgCdTe layers grown by MOCVD on GaAs epi-ready substrates. Infrared Physics and Technology, 2017, 84, 87-93.	2.9	5
52	Uncooled middle wavelength infrared photoconductors based on (111) and (100) oriented HgCdTe. Optical Engineering, 2017, 56, 091602.	1.0	2
53	Engineering steps for optimizing high temperature LWIR HgCdTe photodiodes. Infrared Physics and Technology, 2017, 81, 276-281.	2.9	16
54	The Numericalâ€“Experimental Enhanced Analysis of HOT MCT Barrier Infrared Detectors. Journal of Electronic Materials, 2017, 46, 5471-5478.	2.2	3

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55	InAs/GaSb type-II superlattice infrared detectors: three decades of development. Proceedings of SPIE, 2017, , .	0.8	26
56	Response time improvement of LWIR HOT MCT detectors. Proceedings of SPIE, 2017, , .	0.8	5
57	Theoretical utmost performance of the (1 0 0) long-wave HgCdTe Auger suppressed photodetectors grown on GaAs. Infrared Physics and Technology, 2017, 84, 58-62.	2.9	0
58	Fast Response Hot (111) HGCDTE MWIR Detectors. Metrology and Measurement Systems, 2017, 24, 509-514.	1.4	2
59	InAs/GaSb type-II superlattice infrared detectors: Future prospect. Applied Physics Reviews, 2017, 4, .	11.3	188
60	Response time study in unbiased long wavelength HgCdTe detectors. Optical Engineering, 2017, 56, 1.	1.0	4
61	InAs/GaSb type-II superlattices versus HgCdTe ternary alloys: future prospect. , 2017, , .		3
62	Next decade in infrared detectors. , 2017, , .		54
63	Comparative Study of the Molecular Beam Epitaxial Growth of InAs/GaSb Superlattices on GaAs and GaSb Substrates. Acta Physica Polonica A, 2017, 132, 322-324.	0.5	3
64	Studies of Dark Current Reduction in InAsSb Mid-Wave Infrared HOT Detectors through Two Step Passivation Technique. Acta Physica Polonica A, 2017, 132, 325-328.	0.5	7
65	Infrared devices and techniques. , 2017, , 633-686.		23
66	Advances in Infrared Technology and Applications: introduction. Applied Optics, 2016, 55, ITA1.	2.1	3
67	Status of HgCdTe Barrier Infrared Detectors Grown by MOCVD in Military University of Technology. Journal of Electronic Materials, 2016, 45, 4563-4573.	2.2	12
68	HgCdTe barrier infrared detectors. Progress in Quantum Electronics, 2016, 47, 1-18.	7.0	66
69	Progress in MOCVD growth of HgCdTe epilayers for HOT infrared detectors. Proceedings of SPIE, 2016, , .	0.8	0
70	Recent progress in LWIR HOT photoconductors based on MOCVD grown (100) HgCdTe. Semiconductor Science and Technology, 2016, 31, 105004.	2.0	2
71	Molecular beam epitaxial growth and characterization of InAs layers on GaAs (001) substrate. Optical and Quantum Electronics, 2016, 48, 1.	3.3	15
72	Challenges of small-pixel infrared detectors: a review. Reports on Progress in Physics, 2016, 79, 046501.	20.1	179

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73	Recent progress in MOCVD growth for thermoelectrically cooled HgCdTe medium wavelength infrared photodetectors. Solid-State Electronics, 2016, 118, 61-65.	1.4	9
74	Mid-wave T2SLs InAs/GaSb single pixel PIN detector with GaAs immersion lens for HOT condition. Solid-State Electronics, 2016, 119, 1-4.	1.4	13
75	Low-temperature growth of GaSb epilayers on GaAs (001) by molecular beam epitaxy. Opto-electronics Review, 2016, 24, .	2.4	15
76	Demonstration of Mid-Wave Type-II Superlattice InAs/GaSb Single Pixel Barrier Detector With GaAs Immersion Lens. IEEE Electron Device Letters, 2016, 37, 64-66.	3.9	4
77	p-Type Doping of GaSb by Beryllium Grown on GaAs (001) Substrate by Molecular Beam Epitaxy. Journal of Semiconductor Technology and Science, 2016, 16, 695-701.	0.4	3
78	MOCVD grown HgCdTe p⁺BnN⁺barrier detector for MWIR HOT operation. Proceedings of SPIE, 2015, , .	0.8	2
79	Absence of 1/f noise from diffusion and generation-recombination currents in p-i-n type-II superlattice MWIR detector. , 2015, , .		0
80	Investigation of a near mid-gap trap energy level in mid-wavelength infrared InAs/GaSb type-II superlattices. Semiconductor Science and Technology, 2015, 30, 115004.	2.0	15
81	Engineering the Bandgap of Unipolar HgCdTe-Based nBn Infrared Photodetectors. Journal of Electronic Materials, 2015, 44, 158-166.	2.2	42
82	1/f Noise in Mid-Wavelength Infrared Detectors With InAs/GaSb Superlattice Absorber. IEEE Transactions on Electron Devices, 2015, 62, 2022-2026.	3.0	12
83	MOCVD grown HgCdTe barrier detectors for MWIR high-operating temperature operation. Optical Engineering, 2015, 54, 105105.	1.0	7
84	MWIR barrier detectors versus HgCdTe photodiodes. Infrared Physics and Technology, 2015, 70, 125-128.	2.9	27
85	Infrared Devices And Techniques (Revision). Metrology and Measurement Systems, 2014, 21, 565-618.	1.4	61
86	New trends in infrared and terahertz detectors. , 2014, , .		1
87	nBn T2SLs InAs/GaSb/B-AlGaSb HOT detector for fast frequency response operation. , 2014, , .		1
88	MOCVD Grown HgCdTe Barrier Structures for HOT Conditions (July 2014). IEEE Transactions on Electron Devices, 2014, 61, 3803-3807.	3.0	23
89	Performance comparison of barrier detectors and HgCdTe photodiodes. Proceedings of SPIE, 2014, , .	0.8	1
90	Performance comparison of barrier detectors and HgCdTe photodiodes. Optical Engineering, 2014, 53, 106105.	1.0	15

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91	Mid-wavelength infrared type-II InAs/GaSb superlattice interband cascade photodetectors. Optical Engineering, 2014, 53, 043107.	1.0	28
92	Theoretical modeling of InAsSb/AlAsSb barrier detectors for higher-operation-temperature conditions. Optical Engineering, 2014, 53, 017106.	1.0	14
93	Theoretical modelling of mercury cadmium telluride midâ€wave detector for high temperature operation. IET Optoelectronics, 2014, 8, 239-244.	3.3	1
94	Performance limits of the mid-wave InAsSb/AlAsSb nBn HOT infrared detector. Optical and Quantum Electronics, 2014, 46, 581-591.	3.3	17
95	Modeling of HOT (111) HgCdTe MWIR detector for fast response operation. Optical and Quantum Electronics, 2014, 46, 1303-1312.	3.3	9
96	Fundamental limits of MWIR HgCdTe barrier detectors operating under non-equilibrium mode. Solid-State Electronics, 2014, 100, 20-26.	1.4	7
97	MOCVD grown MWIR HgCdTe detectors for high operation temperature conditions. Opto-electronics Review, 2014, 22, .	2.4	3
98	Mid-Wavelength Infrared nBn for HOT Detectors. Journal of Electronic Materials, 2014, 43, 2963-2969.	2.2	14
99	Barrier infrared detectors. Opto-electronics Review, 2014, 22, .	2.4	81
100	New concepts in infrared photodetector designs. Applied Physics Reviews, 2014, 1, 041102.	11.3	205
101	Semiconductor detectors and focal plane arrays for far-infrared imaging. Opto-electronics Review, 2013, 21, .	2.4	28
102	Changes in the boards of Opto-electronics review. Opto-electronics Review, 2013, 21, .	2.4	0
103	MWIR type-II InAs/GaSb superlattice interband cascade photodetectors. , 2013, , .		4
104	Analysis of the response time in high-temperature LWIR HgCdTe photodiodes operating in non-equilibrium mode. Infrared Physics and Technology, 2013, 61, 162-166.	2.9	8
105	Low-frequency noise in type-II superlattice MWIR nBn detector. , 2013, , .		4
106	HOT infrared photodetectors. Opto-electronics Review, 2013, 21, .	2.4	81
107	Modelling of MWIR HgCdTe complementary barrier HOT detector. Solid-State Electronics, 2013, 80, 96-104.	1.4	35
108	Modeling of InAsSb/AlAsSb nBn HOT detector's performance limit. Proceedings of SPIE, 2013, , .	0.8	10

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109	Theoretical Modeling of HOT HgCdTe Barrier Detectors for the Mid-Wave Infrared Range. Journal of Electronic Materials, 2013, 42, 3309-3319.	2.2	21
110	Doing Hirsch proud; shaping H-index in engineering sciences. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2013, 61, 5-21.	0.8	7
111	Modeling of midwavelength infrared InAs/GaSb type II superlattice detectors. Optical Engineering, 2013, 52, 061307.	1.0	15
112	MOCVD grown HgCdTe device structure for ambient temperature LWIR detectors. Semiconductor Science and Technology, 2013, 28, 105017.	2.0	27
113	Theoretical modelling of MWIR thermoelectrically cooled nBn HgCdTe detector. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2013, 61, 211-220.	0.8	4
114	Modeling of HgCdTe LWIR detector for high operation temperature conditions. Metrology and Measurement Systems, 2013, 20, 159-170.	1.4	13
115	Advanced Infrared Technology and Applications. Advances in Optical Technologies, 2013, 2013, 1-2.	0.8	1
116	The bulk generation-recombination processes and the carrier lifetime in mid-wave infrared and long-wave infrared liquid nitrogen cooled HgCdTe alloys. Journal of Applied Physics, 2012, 112, .	2.5	26
117	Performance modeling of MWIR InAs/GaSb/Bâ€“Al0.2Ga0.8Sb type-II superlattice nBn detector. Semiconductor Science and Technology, 2012, 27, 055002.	2.0	28
118	Numerical Estimations of Carrier Generationâ€“Recombination Processes and the Photon Recycling Effect in HgCdTe Heterostructure Photodiodes. Journal of Electronic Materials, 2012, 41, 2766-2774.	2.2	25
119	Progress in focal plane array technologies. Progress in Quantum Electronics, 2012, 36, 342-473.	7.0	209
120	Dark current modeling of MWIR type-II superlattice detectors. , 2012, , .		11
121	Contribution of Series Resistance in Modelling of High-Temperature Type II Superlattice p-i-n Photodiodes. Advances in Optical Technologies, 2012, 2012, 1-5.	0.8	1
122	Simplified model of dislocations as a SRH recombination channel in the HgCdTe heterostructures. Infrared Physics and Technology, 2012, 55, 98-107.	2.9	32
123	History of infrared detectors. Opto-electronics Review, 2012, 20, .	2.4	309
124	Terahertz detectors and focal plane arrays. Opto-electronics Review, 2011, 19, .	2.4	260
125	Near-room temperature MWIR HgCdTe photodiodes limited by vacancies and dislocations related to Shockleyâ€“Readâ€“Hall centres. Solid-State Electronics, 2011, 63, 8-8.	1.4	7
126	Recent progress in infrared detector technologies. Infrared Physics and Technology, 2011, 54, 136-154.	2.9	419

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127	Improvement in performance of high-operating temperature HgCdTe photodiodes. Infrared Physics and Technology, 2011, 54, 310-315.	2.9	17
128	Numerical estimations of carrier generation-recombination processes and photon recycling effect in 3-<inline-formula><tex-math>${m mu}$</tex-math><math altimg="m1.gif" overflow="scroll"><mrow><mi mathvariant="bold-italic">Î¼</mi></mrow></math></inline-formula>m n-on-p HgCdTe photodiodes. Optical Engineering, 2011, 50, 061003.	1.0	18
129	Novel uncooled infrared detectors. Opto-electronics Review, 2010, 18, .	2.4	4
130	Control of acceptor doping in MOCVD HgCdTe epilayers. Opto-electronics Review, 2010, 18, .	2.4	11
131	History of HgTe-based photodetectors in Poland. Opto-electronics Review, 2010, 18, .	2.4	0
132	High frequency response of near-room temperature LWIR HgCdTe heterostructure photodiodes. Opto-electronics Review, 2010, 18, .	2.4	11
133	THz detectors. Progress in Quantum Electronics, 2010, 34, 278-347.	7.0	258
134	Enhanced numerical analysis of current-voltage characteristics of long wavelength infrared n-on-p HgCdTe photodiodes. Journal of Applied Physics, 2010, 108, .	2.5	36
135	Recent progress in third generation infrared detectors. Journal of Modern Optics, 2010, 57, 1716-1730.	1.3	17
136	Enhanced numerical analysis of current-voltage characteristics of long wavelength infrared p-on-n HgCdTe photodiodes. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2010, 58, .	0.8	3
137	Performance limits of room-temperature InAsSb photodiodes. , 2010, , .		4
138	Influence of TDMAAs Acceptor Precursor on Performance Improvement of HgCdTe Photodiodes. Acta Physica Polonica A, 2010, 118, 1199-1204.	0.5	1
139	Insight on quantum dot infrared photodetectors. Journal of Physics: Conference Series, 2009, 146, 012030.	0.4	7
140	New material systems for third generation infrared detectors. , 2009, , .		11
141	Generation-Recombination Effect in High-Temperature HgCdTe Heterostructure Nonequilibrium Photodiodes. Journal of Electronic Materials, 2009, 38, 1666-1676.	2.2	12
142	Outlook on quantum dot infrared photodetectors. Optical Memory and Neural Networks (Information Optics), 2009, 18, 234-252.	1.0	1
143	Insight into performance of quantum dot infrared photodetectors. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2009, 57, .	0.8	25
144	Third-generation infrared photodetector arrays. Journal of Applied Physics, 2009, 105, .	2.5	672

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145	Surface smoothness improvement of HgCdTe layers grown by MOCVD. Bulletin of the Polish Academy of Sciences: Technical Sciences, 2009, 57, .	0.8	7
146	Morphology issues of HgCdTe samples grown by MOCVD. Proceedings of SPIE, 2009, , .	0.8	3
147	HgTe-based photodetectors in Poland. Proceedings of SPIE, 2009, , .	0.8	0
148	Infrared Detectors for the Future. Acta Physica Polonica A, 2009, 116, 389-406.	0.5	111
149	Quantum-dot infrared photodetectors: Status and outlook. Progress in Quantum Electronics, 2008, 32, 89-120.	7.0	227
150	Two-colour HgCdTe infrared detectors operating above 200 K. Opto-electronics Review, 2008, 16, .	2.4	4
151	New material systems for third generation infrared photodetectors. Opto-electronics Review, 2008, 16, .	2.4	69
152	Assessment of quantum dot infrared photodetectors for high temperature operation. Journal of Applied Physics, 2008, 104, 034314.	2.5	47
153	Comparison of performance of quantum dot and other types of infrared photodetectors. Proceedings of SPIE, 2008, , .	0.8	17
154	Variation of pKa in the N-Terminal Tyrosine Side Chain in Octapeptide Analogs of Tendamistat Influences α-Amylase Inhibition. Protein and Peptide Letters, 2007, 14, 497-501.	0.9	1
155	Enhanced numerical analysis of three-color HgCdTe detectors. , 2007, , .		5
156	Progress in MOCVD growth of HgCdTe heterostructures for uncooled infrared photodetectors. Infrared Physics and Technology, 2007, 49, 173-182.	2.9	50
157	Material considerations for third generation infrared photon detectors. Infrared Physics and Technology, 2007, 50, 240-252.	2.9	74
158	Numerical analysis of three-colour HgCdTe detectors. Opto-electronics Review, 2007, 15, .	2.4	5
159	High-Operating-Temperature Infrared Photodetectors. , 2007, , .		105
160	Model and clinical studies of a novel differential lung ventilation system for adults. Critical Care, 2006, 10, P30.	5.8	2
161	Competitive technologies for third generation infrared photon detectors. , 2006, , .		10
162	InAs/GaInSb superlattices as a promising material system for third generation infrared detectors. Infrared Physics and Technology, 2006, 48, 39-52.	2.9	124

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163	Unique differential lung ventilation system. Journal of Biomechanics, 2006, 39, S589.	2.1	0
164	Competitive technologies of third generation infrared photon detectors. Opto-electronics Review, 2006, 14, .	2.4	45
165	Temperature dependent current-voltage characteristics of MWIR HgCdTe photodiodes operated at higher temperatures. , 2005, 5957, 360.		0
166	Improvements in MOCVD growth of Hg 1-x Cd x Te heterostructures for uncooled infrared photodetectors. , 2005, , .		6
167	InAs/GaInSb superlattices as a promising material system for third generation infrared detectors. , 2005, 5834, 1.		1
168	MOCVD HgCdTe heterostructures for uncooled infrared photodetectors. , 2005, , .		19
169	HgCdTe infrared detector material: history, status and outlook. Reports on Progress in Physics, 2005, 68, 2267-2336.	20.1	787
170	Uncooled long-wavelength infrared photon detectors. , 2004, , .		5
171	Uncooled long wavelength infrared photon detectors. Infrared Physics and Technology, 2004, 46, 115-131.	2.9	107
172	Toward third generation HgCdTe infrared detectors. Journal of Alloys and Compounds, 2004, 371, 53-57.	5.5	76
173	Minority carrier lifetime and noise in abrupt molecular-beam epitaxy-grown HgCdTe heterostructures. Journal of Electronic Materials, 2003, 32, 639-645.	2.2	4
174	Chairman's Preface. Crystal Research and Technology, 2003, 38, 199-199.	1.3	0
175	Infrared detectors: status and trends. Progress in Quantum Electronics, 2003, 27, 59-210.	7.0	960
176	Quantum well photoconductors in infrared detector technology. Journal of Applied Physics, 2003, 93, 4355-4391.	2.5	251
177	Third-generation infrared photon detectors. Optical Engineering, 2003, 42, 3498.	1.0	26
178	Competition of infrared detector technologies. , 2003, , .		3
179	HgCdTe infrared detectors: historical prospect. , 2003, , .		3
180	<title>Quantum well infrared photoconductors in infrared detectors technology</title>. , 2003, , .		0

#	Article	IF	Citations
181	<title>Analysis of VLWIR HgCdTe photodiode performance</title>. , 2003, , .		0
182	QUANTUM WELL INFRARED PHOTOCONDUCTORS IN INFRARED DETECTORS TECHNOLOGY. Selected Topics in Electornics and Systems, 2003, , 1-66.	0.2	1
183	QUANTUM WELL INFRARED PHOTOCONDUCTORS IN INFRARED DETECTORS TECHNOLOGY. International Journal of High Speed Electronics and Systems, 2002, 12, 593-658.	0.7	4
184	Surface leakage current in HgCdTe photodiodes. , 2002, , .		4
185	Comparison of performance limits of infrared detector materials. , 2002, 4650, 117.		6
186	Comparison of photon and thermal detector performance. , 2002, , 5-81.		10
187	Numerical modeling of fluctuation phenomena in semiconductors and detailed noise study of mid-wave infrared HgCdTe-heterostructure devices. Journal of Electronic Materials, 2002, 31, 677-682.	2.2	6
188	HgCdTe buried multi-junction photodiodes fabricated by the liquid phase epitaxy. Infrared Physics and Technology, 2002, 43, 157-163.	2.9	13
189	Infrared detectors: an overview. Infrared Physics and Technology, 2002, 43, 187-210.	2.9	606
190	Heterostructure HgCdTe photovoltaic detectors. , 2001, 4355, 1.		1
191	<title>HgCdTe buried multiple photodiodes fabricated by the liquid phase epitaxy</title>. , 2001, , .		1
192	Infrared detectors at the beginning of the next millennium. , 2001, , .		8
193	Materials science and applications of solid crystals. III-Vs Review, 2001, 14, 46-50.	0.0	0
194	Two-dimensional analysis of double-layer heterojunction HgCdTe photodiodes. IEEE Transactions on Electron Devices, 2001, 48, 1326-1332.	3.0	79
195	<title>Two-dimensional analysis of double-layer heterojunction HgCdTe photodiodes</title>. , 2001, 4288, 335.		4
196	Computer modeling of dual-band HgCdTe photovoltaic detectors. Journal of Applied Physics, 2001, 90, 1286-1291.	2.5	29
197	Hg-based alternatives to MCT. , 2001, , 377-400.		5
198	Mercury Cadmium Telluride Photodiodes at the Beginning of the Next Millennium (Review Paper). Defence Science Journal, 2001, 51, 5-34.	0.8	13

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199	High-sensitivity 8- to 14-Î¼m HgCdTe photodetectors operated at ambient temperature. , 2000, 3948, 94.		2
200	Dual-band infrared focal plane arrays. , 2000, 4340, 1.		2
201	Computer modeling of dual-band HgCdTe photovoltaic detectors. , 2000, , .		0
202	Heterostructure infrared photovoltaic detectors. Infrared Physics and Technology, 2000, 41, 213-238.	2.9	38
203	Effect of dislocations on performance of LWIR HgCdTe photodiodes. Journal of Electronic Materials, 2000, 29, 736-741.	2.2	46
204	LPE growth of Hg 1-x Cd x Te heterostructures using a novel tipping boat. , 2000, 3948, 382.		2
205	Dual-band infrared detectors. , 2000, 3948, 17.		8
206	Narrow-Gap Semiconductor Photodiodes. , 2000, , .		46
207	Narrow-Gap Semiconductor Materials. , 2000, , .		28
208	Heterostructure infrared photodiodes. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2000, 3, 111-120.	1.0	5
209	<title>Performance limitations of InGaAs photodiodes</title>. , 1999, , .		0
210	<title>Liquid-phase epitaxial growth and characterization of In(Sb,Bi)</title>. , 1999, , .		3
211	Computer simulation of HgCdTe photovoltaic devices based on complex heterostructures. , 1999, 3629, 74.		7
212	InGaAs versus HgCdTe for short-wavelength infrared applications. , 1999, , .		2
213	Assessment of HgCdTe photodiodes and quantum well infrared photoconductors for long wavelength focal plane arrays. Infrared Physics and Technology, 1999, 40, 279-294.	2.9	46
214	Performance limitation of short wavelength infrared InGaAs and HgCdTe photodiodes. Journal of Electronic Materials, 1999, 28, 630-636.	2.2	30
215	HgCdTe photodiode passivated with a wide-bandgap epitaxial layer. , 1999, 3629, 416.		3
216	<title>Assessment of HgCdTe photodiodes and quantum well infrared photoconductors for long-wavelength focal plane arrays</title>. , 1999, , .		0

#	Article	IF	Citations
217	Comparison of mercury cadmium telluride LPE layers growth from Te-rich solution on (111)Cd 0.9 5Zn 0.05 Te and (211)Cd 0.9 5Zn 0.05 Te. , 1999, , .		1
218	New generation of infrared photodetectors. Sensors and Actuators A: Physical, 1998, 67, 146-152.	4.1	40
219	<title>Narrow-gap semiconductor photodiodes</title>. , 1998, , .		46
220	<title>RF magnetron sputtering deposition of CdTe passivation on HgCdTe</title>. , 1998, , .		0
221	<title>Comparison of GaN Schottky barrier and p-n junction photodiodes</title>. , 1998, , .		0
222	<title>Comparison of the performance of quantum well and conventional bulk infrared photodetectors</title>. , 1997, , .		2
223	<title>InAsSb heterojunction photodiodes grown by liquid phase epitaxy</title>. , 1997, 3179, 247.		0
224	<title>Infrared thermal detectors versus photon detectors: II. focal plane arrays</title>. , 1997, 3179, 224.		1
225	<title>Influence of doping and geometry on GaN ultraviolet photodiode performance: numerical modeling</title>. , 1997, , .		2
226	<title>Infrared thermal detectors versus photon detectors: I. Pixel performance</title>. , 1997, , .		13
227	<title>AlGaN ultraviolet detectors</title>. , 1997, , .		5
228	Comparison of the performance of quantum well and conventional bulk infrared photodetectors. Infrared Physics and Technology, 1997, 38, 295-310.	2.9	53
229	Photoelectromagnetic, magnetoconcentration, and Dember infrared detectors. , 1997, , 506-525.		3
230	Semiconductor ultraviolet detectors. Journal of Applied Physics, 1996, 79, 7433-7473.	2.5	1,340
231	Semiconductor ultraviolet detectors. , 1996, , .		33
232	Near room-temperature InAsSb photodiodes: Theoretical predictions and experimental data. Solid-State Electronics, 1996, 39, 1593-1600.	1.4	25
233	Comment on â€˜â€˜Temperature limits on infrared detectivities of InAs/InxGa1â^'xSb superlattices and bulk Hg1â^'xCdxTeâ€™â€™ [J. Appl. Phys.74, 4774 (1993)]. Journal of Applied Physics, 1996, 80, 2542-2544.	2.5	29
234	Theoretical modeling of long wavelengthn+â€onâ€pHgCdTe photodiodes. Journal of Applied Physics, 1996, 80, 2483-2489.	2.5	10

#	Article	IF	Citations
235	<title>LWIR p+-n photodiodes fabricated with HgCdTe bulk material</title>. , 1995, 2373, 376.		0
236	<title>Computer modeling of carrier transport in binary lead salt photodiodes</title>. , 1995, , .		1
237	<title>GaAs/AlGaAs quantum well infrared detectors among the other types of semiconductor infrared detectors</title>. , 1995, , .		0
238	<title>Long-wavelength n+-on-p HgCdTe photodiodes: theoretical predictions and experimental data</title>. , 1995, , .		3
239	Erratum to â€œcomputer modelling of carrier transport in PbSnSe photodiodesâ€• Infrared Physics and Technology, 1995, 36, 821.	2.9	0
240	Longâ€wavelength HgCdTe photodiodes:n+â€onâ€pversuspâ€onâ€nstructures. Journal of Applied Physics, 1995, 77, 3505-3512.	2.5	30
241	Photovoltaic effects in GaN structures with pâ€n junctions. Applied Physics Letters, 1995, 67, 2028-2030.	3.3	78
242	Kinetics of photoconductivity in nâ€type GaN photodetector. Applied Physics Letters, 1995, 67, 3792-3794.	3.3	77
243	<title>Characterization of p-on-n HgCdTe diffusion photodiodes</title>. , 1995, , .		0
244	<title>GaAs/AlGaAs quantum well infrared photoconductors versus HgCdTe photodiodes for long-wavelength infrared applications</title>. , 1994, , .		2
245	Guest Editorial: Special Section on Semiconductor Infrared Detectors. Optical Engineering, 1994, 33, 1392.	1.0	12
246	Thermoelectrically cooled arsenic diffused medium-wavelength infrared HgCdTe photodiodes. Optical Engineering, 1994, 33, 1434.	1.0	2
247	New trends in infrared detector technology. Infrared Physics and Technology, 1994, 35, 1-21.	2.9	19
248	Computer modeling of carrier transport in PbSnSe photodiodes. Infrared Physics and Technology, 1994, 35, 837-845.	2.9	1
249	New trends in semiconductor infrared detectors. Optical Engineering, 1994, 33, 1395.	1.0	35
250	GaAs/AlGaAs QWIPs vs HgCdTe Photodiodes for LWIR Applications. , 1994, , 87-96.		1
251	Semiconductor superlattices and quantum wells for infrared optoelectronics. Progress in Quantum Electronics, 1993, 17, 93-164.	7.0	18
252	<title>New ternary alloy systems for infrared detectors</title>. , 1993, , .		15

#	Article	IF	Citations
253	Performance of p+-n HgCdTe photodiodes. Semiconductor Science and Technology, 1993, 8, S289-S292.	2.0	7
254	<title>Quantum-well infrared optoelectronic devices</title>. , 1993, 1845, 61.		0
255	<title>Arsenic diffused p<formula>^{<roman>+</roman>}</formula>-n HgCdTe photodiodes</title>. , 1993, 1845, 171.		0
256	Performance of p+â^'n HgCdTe photodiodes. Infrared Physics, 1992, 33, 463-473.	0.5	18
257	Hg(1â^'x)MnxTe as a new infrared detector material. Infrared Physics, 1991, 31, 117-166.	0.5	60
258	Performance of mercury cadmium telluride photoconductive detectors. Infrared Physics, 1991, 31, 543-554.	0.5	30
259	The performance of Hg1â^'x Zn x Te photodiodes. Applied Physics A: Solids and Surfaces, 1990, 50, 379-384.	1.4	7
260	A modified hot wall epitaxy technique for the growth of CdTe and Hg1â^'xCdxTe epitaxial layers. Thin Solid Films, 1990, 191, 239-245.	1.8	8
261	Hg1â^'xZnxTe as a potential infrared detector material. Progress in Quantum Electronics, 1989, 13, 299-353.	7.0	30
262	The performance of Hg1â^'xMnxTe photodiodes. Infrared Physics, 1989, 29, 887-893.	0.5	6
263	Intrinsic carrier concentration and effective masses in InAs1â^'xSbx. Infrared Physics, 1989, 29, 35-42.	0.5	30
264	Auger-limited carrier lifetime in HgZnTe ambient temperature 10.6Î¼m photoresistors. Infrared Physics, 1989, 29, 149-154.	0.5	4
265	InAs1â^'xSbx infrared detectors. Progress in Quantum Electronics, 1989, 13, 191-231.	7.0	63
266	The Intrinsic Carrier Concentration in Pb1â^'xSnxTe, Pb1â^'xSnxSe, and PbS1â^'xSex. Physica Status Solidi A, 1989, 111, 559-565.	1.7	7
267	Calculation of the carrier lifetime in Hg1â^'xZnxTe. Infrared Physics, 1988, 28, 311-319.	0.5	6
268	Analysis of the R0A product in n+-p Hg1â^'xCdxTe photodiodes. Infrared Physics, 1988, 28, 139-153.	0.5	88
269	Intrinsic carrier concentrations and effective masses in the potential infrared detector material, Hg1â^'xZnxTe. Infrared Physics, 1988, 28, 101-107.	0.5	24
270	Influence of dislocations on the performance of Hg1â^'xCdxTe graded gap photoresistors. Infrared Physics, 1988, 28, 279-286.	0.5	8

#	Article	IF	Citations
271	Intrinsic infrared detectors. Progress in Quantum Electronics, 1988, 12, 87-289.	7.0	158
272	Band-to-band recombination in GaxIn1â˜'xSb. Infrared Physics, 1987, 27, 353-360.	0.5	4
273	Calculation of the intrinsic carrier concentration in InAs_{1â€xâ€x}^{Sb}. Physica Status Solidi (B): Basic Research, 1986, 135, K85.	1.5	6
274	On the Performance of Non-Cooled (In, As)Sb Photoelectromagnetic Detectors for 10.6 m Radiation. Physica Status Solidi A, 1985, 91, 745-751.	1.7	3
275	Band-to-band recombination in InAs1â˜'xSbx. Infrared Physics, 1985, 25, 551-560.	0.5	48
276	PbS1-x,Sex, (Oâ©½x â©½1) photovoltaic detectors: carrier lifetimes and resistance-area product. Infrared Physics, 1983, 23, 23-32.	0.5	4
277	PbTe photodiodes prepared by the hot-wall evaporation technique. Thin Solid Films, 1983, 103, 343-353.	1.8	0
278	PbTe photodiodes prepared by the hot-wall evaporation technique. Thin Solid Films, 1983, 103, 343-353.	1.8	3
279	Effect of structure on the quantum efficiency and R0A product of lead-tin chalcogenide photodiodes. Infrared Physics, 1982, 22, 199-208.	0.5	21
280	Photovoltaic detectors Pb1â˜'xSnxTe (0â©½x â©½ 0.25). Minority carrier lifetimes. Resistance-area product. Infrared Physics, 1981, 21, 1-8.	0.5	6
281	Photovoltaic detectors Pb1â˜'xSnxSe (0 â©½ x â©½ 0.12). Minority carrier lifetimes. Resistance-area product. Infrared Physics, 1981, 21, 251-259.	0.5	6
282	Temperature dependence of the RoA product for lead chalcogenide photovoltaic detectors. Infrared Physics, 1981, 21, 191-199.	0.5	11
283	Influence of air on the electrical properties of Pb1-xSnxTe layers on a mica substrate. Thin Solid Films, 1980, 74, 59-68.	1.8	5
284	Detectivity limits for PbTe photovoltaic detectors. Infrared Physics, 1980, 20, 223-229.	0.5	8
285	heterojunctions prepared by a modified hot wall technique. Thin Solid Films, 1980, 67, 179-186.	1.8	3
286	2.22 Electrical and piezoresistive properties of Pb1â˜'xSnxTe thin films. Vacuum, 1977, 27, 317-319.	3.5	0
287	History of HgTe-based photodetectors in Poland. Opto-electronics Review, 0, , .	2.4	1
288	HgCdTe versus Other Material Systems: A Historical Look. , 0, , .		0